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CERTIFICATE OF MAILING

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Kristi L. Davidson

Kristi L. Davidson, Reg. No. 44,643

8/9/05

Date

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Serial No.: 10/797,876
Filed: March 10, 2004
Group Art Unit: 2813
Examiner: Jennifer M. Dolan
Applicant: Anthony Dip et al.
Title: **SILICON GERMANIUM SURFACE LAYER FOR HIGH-K
DIELECTRIC INTEGRATION**
Attorney Docket: TPS-007
Confirmation No.: 5070

Cincinnati, Ohio 45202

August 9, 2005

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

In accordance with the duty of candor and good faith imposed by 37 C.F.R. §1.56, and means of complying therewith according to 37 C.F.R. §§1.97 and 1.98, the references listed on the attached Form PTO-1449 are called to the attention of the United States Patent and Trademark

Application Serial No. 10/797,876
Supplemental Information Disclosure Statement
submitted August 9, 2005
from International Search Report of PCT/US2005/000661

Office in connection with the above-identified patent application. Because the requirement (37 C.F.R. §1.98(a)(2)(i)) for submitting copies of U.S. patents and published applications has been waived, copies of only the foreign cited references and/or other documents are enclosed herewith. Applicants have also enclosed a copy of the foreign Search Report listing these references. It is noted that U.S. Patent Publication No. US 2001/0055888 A1 has now issued as U.S. Patent No. 6,488,777, and therefore is referenced as such on the Form PTO-1449.

It is submitted that the cited references do not disclose or render obvious the subject matter claimed in the present application.

Certifications under 37 C.F.R. § 1.97(e) and § 1.704(d)

Each item of information contained in the information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement.

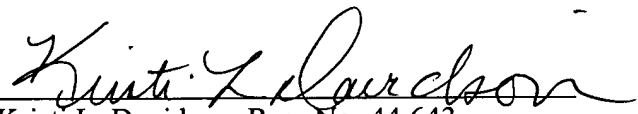
Each item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart application and to the knowledge of the person signing the certification after making reasonable inquiry, no item of information contained in the information disclosure statement was known to any individual designated in 37 C.F.R. § 1.56(c) more than thirty days prior to the filing of the information disclosure statement.

Application Serial No. 10/797,876
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Applicants do not believe that any fees are due in connection with this submission.
However, if such petition is due or any fees are necessary, the Commissioner may consider this to
be a request for such and charge any necessary fees to Deposit Account No. 23-3000.

Respectfully submitted,

WOOD, HERRON & EVANS, L.L.P.

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SUBSTITUTE FORM PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. TPS-007		SERIAL NO. 10/797,876	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				APPLICANT Anthony Dip et al.			
				FILING DATE March 10, 2004		GROUP 2813	

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		PATENT NUMBER							ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A.A	5	2	5	9	8	8	1	11/09/1993	Edwards et al.	118	719	05/17/1991
	A.B	6	2	9	6	7	1	1	10/02/2001	Loan et al.	118	726	10/20/1999
	A.C	6	4	8	8	7	7	7	12/03/2002	Madan et al.	118	718	04/03/2001
	A.D												
	A.E												
	A.F												
	A.G												
	A.H												
	A.I												
	A.J												
	A.K												

FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS

		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
	A.L						
	A.M						
	A.N						
	A.O						
	A.P						
	A.Q						

OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)

	A.R	Cho et al., <u>Interfacial Characteristics of HfO₂ Films Grown on Strained Si_{0.7}Ge_{0.3} by Atomic-Layer Deposition</u> , Applied Physics Letters, Vol. 84, No. 7, 02/16/2004, pp. 1171-1173
	A.S	J. Westlinder et al., <u>Effects of Low-Temperature Water Vapor Annealing of Strained SiGe Surface-Channel pMOSFETs with High-k Dielectric</u> , European Solid-State Device Research, 09/16/2003, pp. 525-528
	A.T	S. Pal et al., <u>Gd₂O₃, Ga₂O₃(Gd₂O₃), Y₂O₃, and Ga₂O₃, as High-k Gate Dielectrics on SiGe: A Comparative Study</u> , J. Applied Physics, Vol. 90, No. 8, 10/15/2001, pp. 4103-4107

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not in conformance. Draw line through citation only if not in conformance and not considered. Include a copy of this form with next communication to Applicant.

SUBSTITUTE FORM PTO-1449 (MODIFIED)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. TPS-007		SERIAL NO. 10/797,876	
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EXAMINER INITIAL		PATENT NUMBER	ISSUE DATE	PATENTEE	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	B.A						
	B.B						
	B.C						
	B.D						
	B.E						
	B.F						
	B.G						
	B.H						
	B.I						
	B.J						
	B.K						
FOREIGN PATENTS OR PUBLISHED FOREIGN PATENT APPLICATIONS							
		DOCUMENT NUMBER	PUBLICATION DATE	COUNTRY OR PATENT OFFICE	CLASS	SUBCLASS	TRANSLATION (YES/NO)
	B.L						
	B.M						
	B.N						
	B.O						
	B.P						
	B.Q						
OTHER DOCUMENTS (Including Author, Title, Date, Place of Publication)							
	B.R	Choi et al., <u>Electrical Characteristics of ZrO₂ Gate Dielectric Deposited on Ultrathin Silicon Capping Layer for SiGe Metal-Oxide-Semiconductor Device Applications</u> , Jpn. J. Appl. Physics, Part 1, Vol 41, No. 8, Aug 2002, pp. 5129-5130					
	B.S	Chatterjee et al., <u>Electrical Properties of Stacked Gate Dielectric (SiO₂/ZrO₂) Deposited on Strained SiGe Layers</u> , Thin Solid Films, Vol. 422, No. 1-2, 12/20/2002, pp. 33-38					
	B.T	European Patent Office, <u>International Search Report</u> , PCT/US2005/000661, Dated 7/27/2005, 5 pp.					
EXAMINER				DATE CONSIDERED			
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